

EUROPEAN PATENT OFFICE

Patent Abstracts of Japan

PUBLICATION NUMBER : 02224336
PUBLICATION DATE : 06-09-90

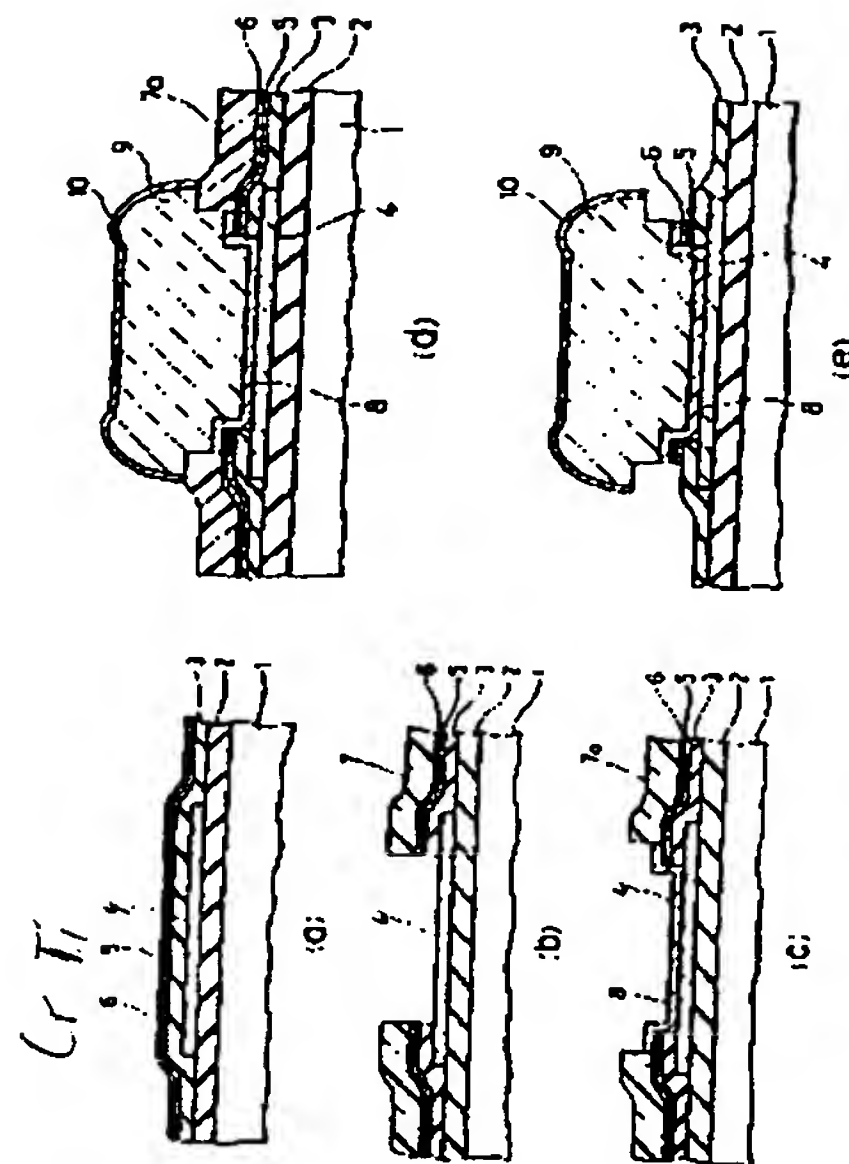
APPLICATION DATE : 27-02-89
APPLICATION NUMBER : 01047773

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INT.CL. : H01L 21/321 H01L 21/306

TITLE : MANUFACTURE OF
SEMICONDUCTOR DEVICE



ABSTRACT : **PURPOSE:** To prevent corrosion of a pad electrode consisting of Al or the like by a method wherein a bump type electrode layer is formed on an adhesion barrier metal layer by an electrolytic plating method and the metal layer is removed using this electrode layer as a mask.

CONSTITUTION: A silicon oxide film 2 is formed on the whole surface of a semiconductor substrate 1 and an Al pad electrode 4 is selectively formed on this film 2. After that, an insulating film 3, such as a silicon oxide film and the like, is formed on the whole surface including the electrode 4 and metal layers 5 and 6 are formed in order on this film 3. Then, after a P-type photosensitive resin film 7 is formed on the whole surface, the region, where is located on the electrode 4, of the film 7 is selectively opened. A plurality of the metal layers 5 and 6 and the film 3 are etched away in order to make the electrode 4 expose. Then, parts, which match to a first opening part of a first mask, of the layers 5 and 6 are removed, then, an adhesion barrier metal layer 8 is formed in a second opening part of a second mask. In this case, the layer 8 is superposed on the edge parts, which are located on the sides of the opening parts, of the layers 5 and 6 at its edge parts and the layer 8 and the layers 5 and 6 are electrically connected to each other. Thereby, corrosion of a pad electrode is avoided.

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